

MOSFET

650V CoolMOS™ E6 Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ E6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC qualified, Pb-free plating, Halogen free mold compound

Potential applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV and Lighting, Server, Telecom and UPS

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

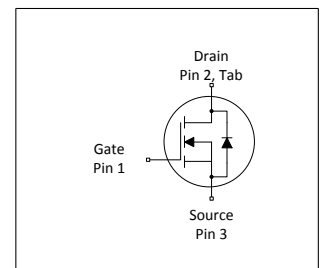


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	600	$m\Omega$
$Q_{g,typ}$	23	nC
$I_{D,pulse}$	18	A
$E_{oss}@400V$	2	μJ
Body diode di/dt	500	$A/\mu s$

Type / Ordering Code	Package	Marking	Related Links
IPS65R600E6	PG-TO 251-3	65E6600	see Appendix A

Table of Contents

Description	1
Maximum ratings	3
Thermal characteristics	4
Electrical characteristics	5
Electrical characteristics diagrams	7
Test Circuits	11
Package Outlines	12
Appendix A	13
Revision History	14
Trademarks	14
Disclaimer	14

1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	7.3 4.6	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	18	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	142	mJ	$I_D=1.3\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	0.21	mJ	$I_D=1.3\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, repetitive	I_{AR}	-	-	1.3	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots480\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	63	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	6.3	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	18	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di _f /dt	-	-	500	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	2	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	2.5	3.0	3.5	V	$V_{DS}=V_{GS}, I_D=0.21mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=650, V_{GS}=0V, T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.54 1.40	0.60	Ω	$V_{GS}=10V, I_D=2.1A, T_j=25^\circ\text{C}$ $V_{GS}=10V, I_D=2.1A, T_j=150^\circ\text{C}$
Gate resistance	R_G	-	10.5	-	Ω	$f=1\text{MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	440	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Output capacitance	C_{oss}	-	30	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	21	-	pF	$V_{GS}=0V, V_{DS}=0\dots480V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	88	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0\dots480V$
Turn-on delay time	$t_{d(on)}$	-	10	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=3.2A,$ $R_G=6.8\Omega$; see table 9
Rise time	t_r	-	8	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=3.2A,$ $R_G=6.8\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	64	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=3.2A,$ $R_G=6.8\Omega$; see table 9
Fall time	t_f	-	11	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=3.2A,$ $R_G=6.8\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{GS}	-	2.75	-	nC	$V_{DD}=480V, I_D=3.2A, V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	12	-	nC	$V_{DD}=480V, I_D=3.2A, V_{GS}=0$ to 10V
Gate charge total	Q_g	-	23	-	nC	$V_{DD}=480V, I_D=3.2A, V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	5.5	-	V	$V_{DD}=480V, I_D=3.2A, V_{GS}=0$ to 10V

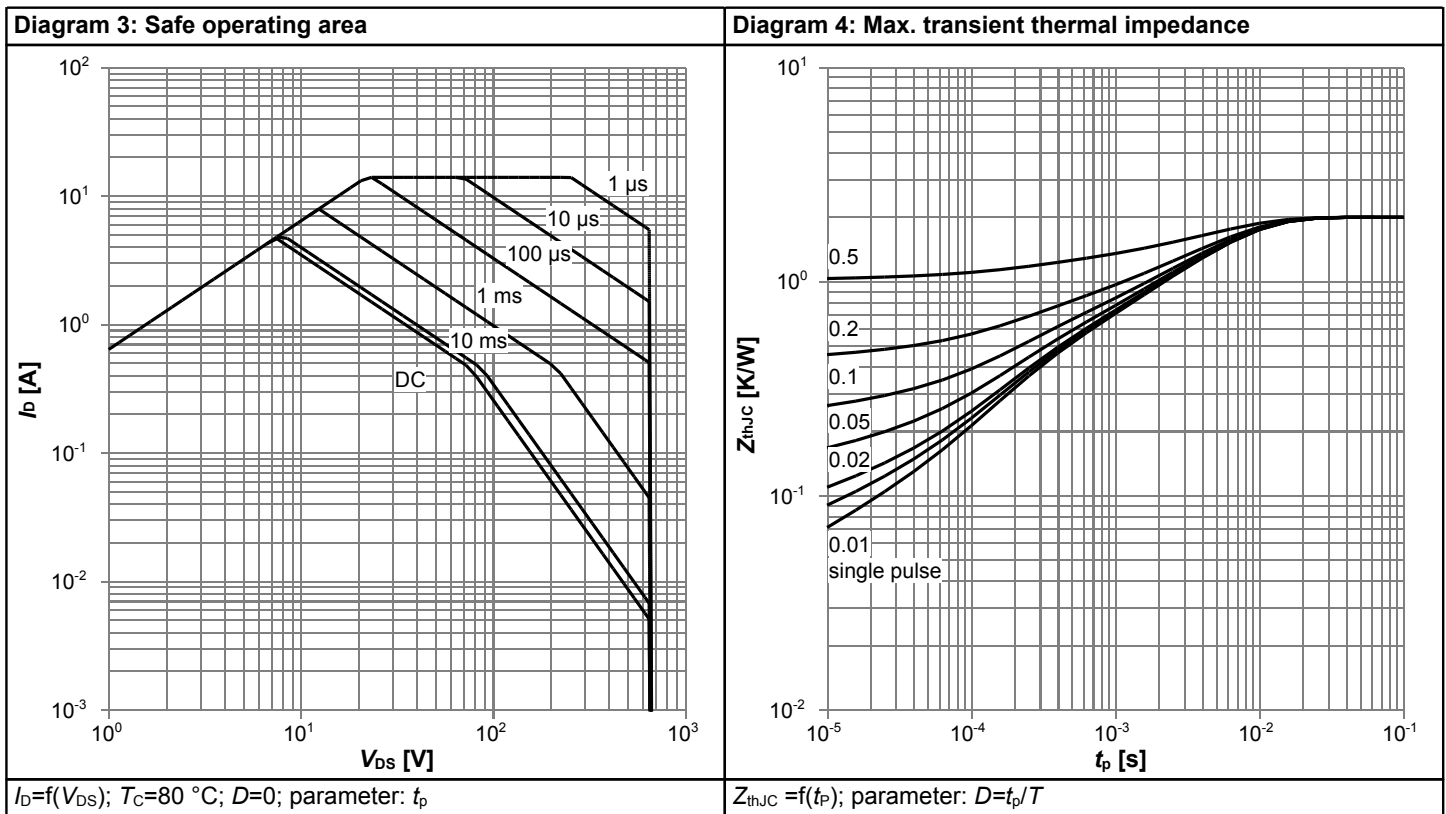
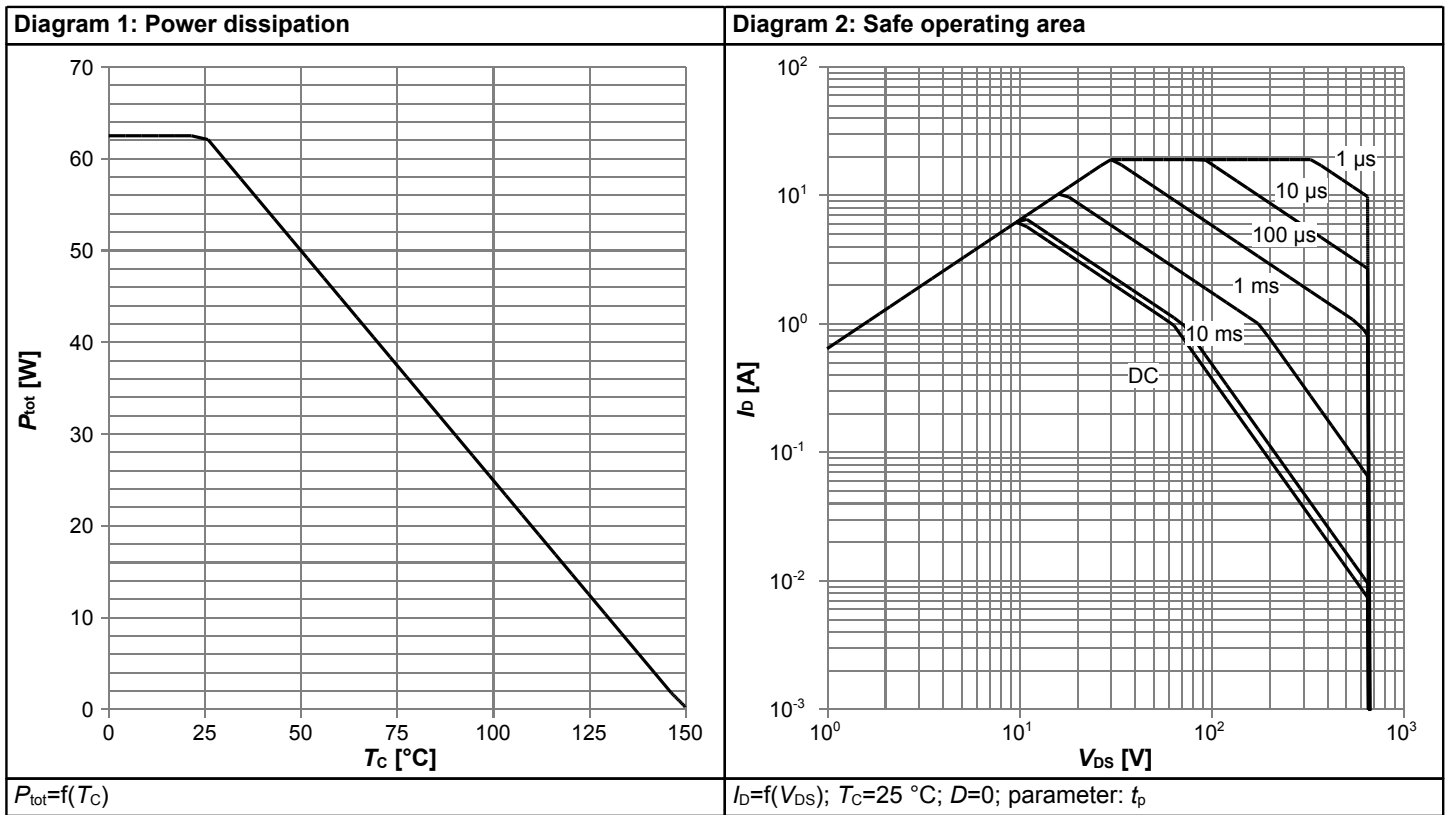
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 480V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 480V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=3.2A, T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	270	-	ns	$V_R=400V, I_F=3.2A, di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	2	-	μC	$V_R=400V, I_F=3.2A, di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	13	-	A	$V_R=400V, I_F=3.2A, di_F/dt=100A/\mu s$; see table 8

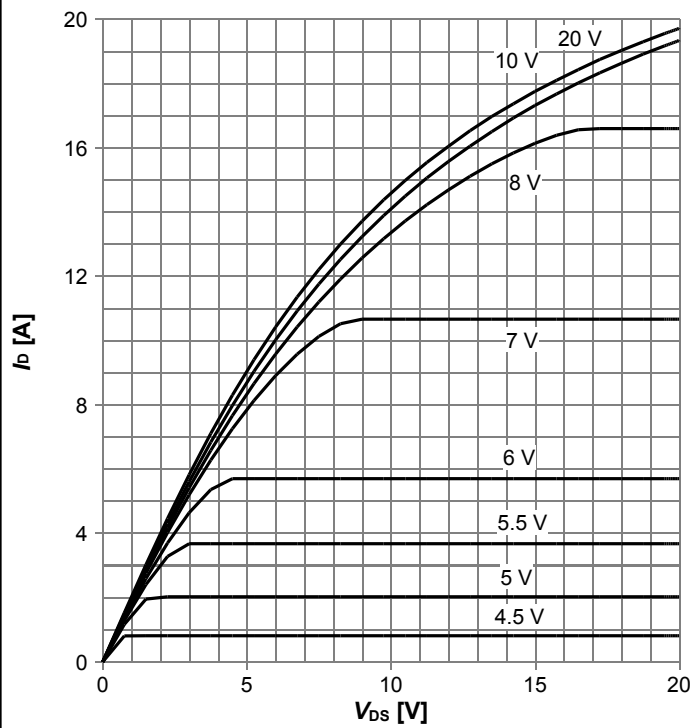
4 Electrical characteristics diagrams



650V CoolMOS™ E6 Power Transistor

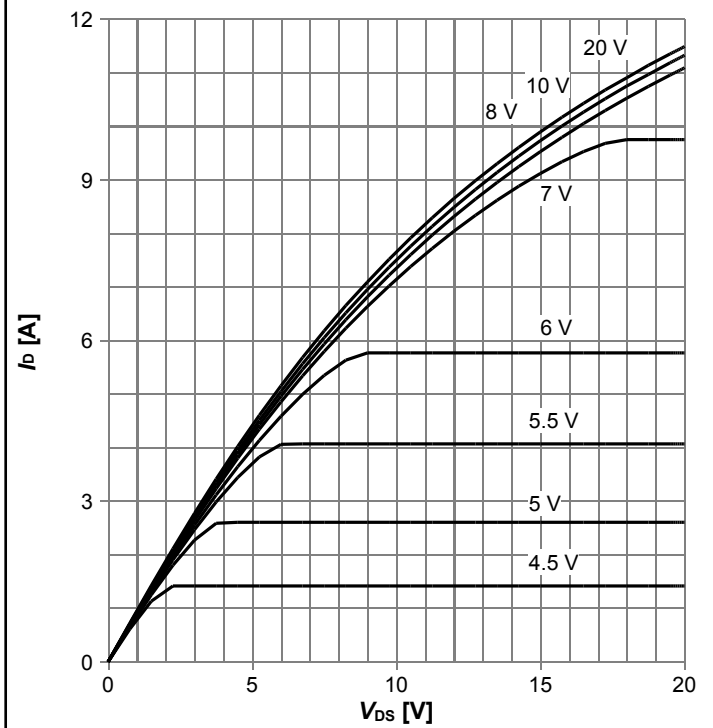
IPS65R600E6

Diagram 5: Typ. output characteristics



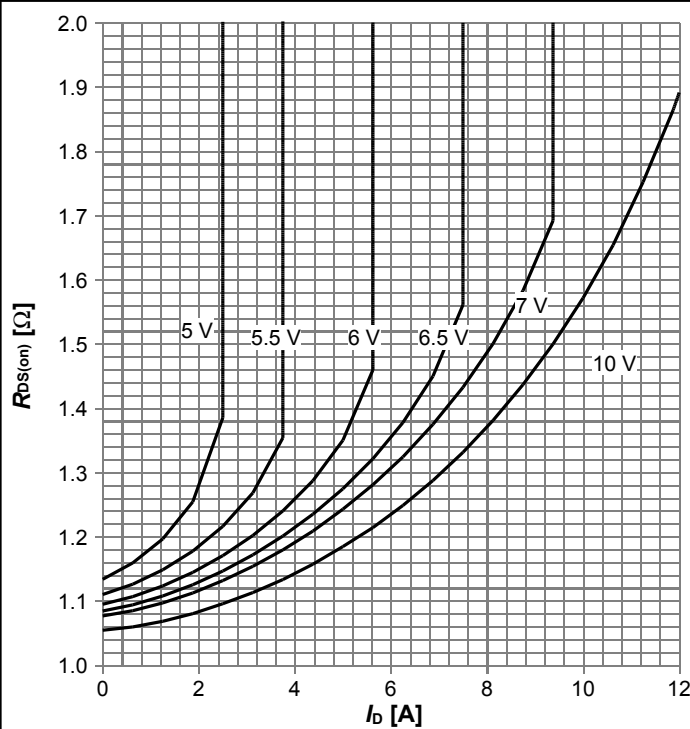
$I_D=f(V_{DS})$; $T_j=25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



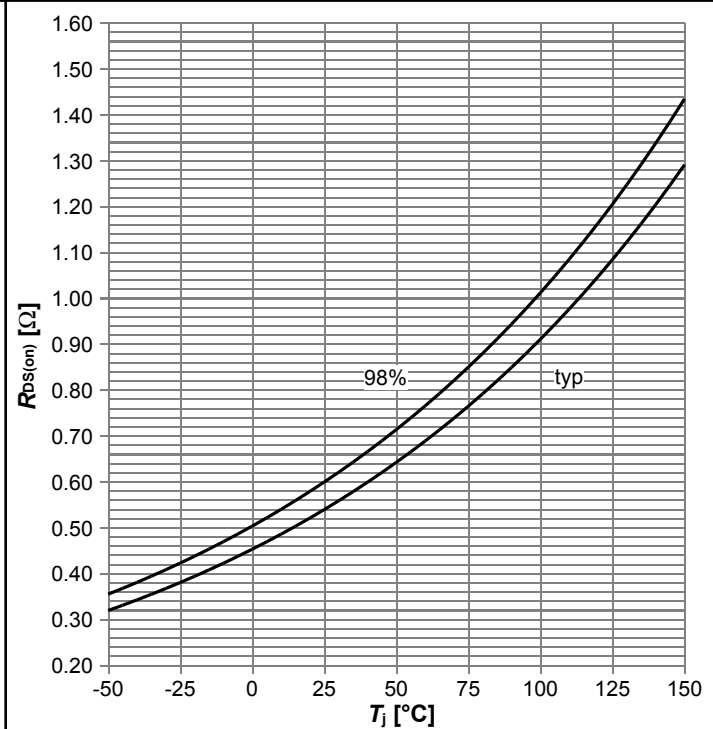
$I_D=f(V_{DS})$; $T_j=125\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



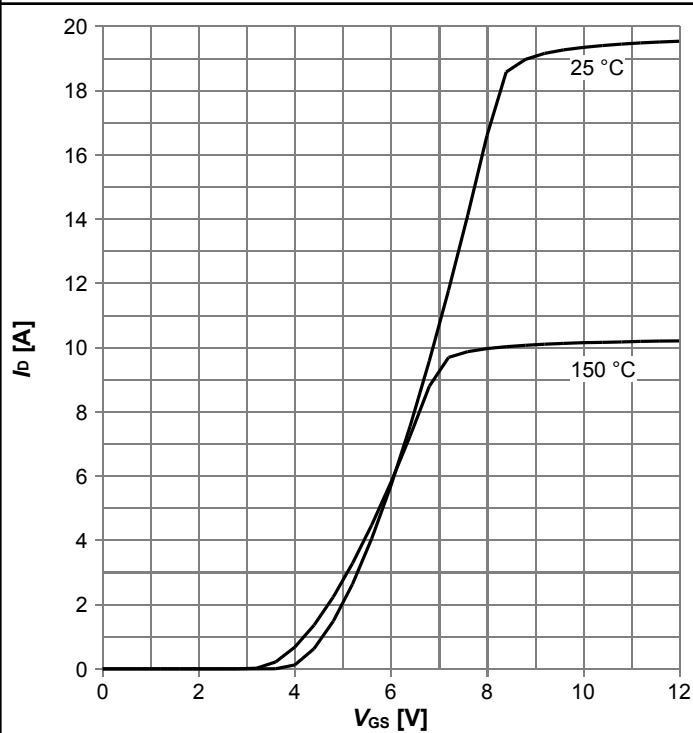
$R_{DS(on)}=f(I_D)$; $T_j=125\text{ °C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



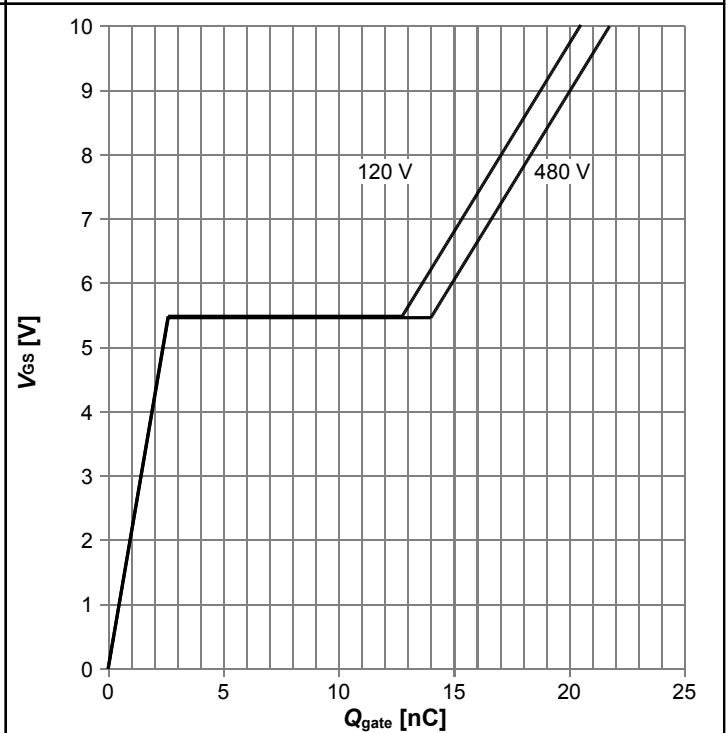
$R_{DS(on)}=f(T_j)$; $I_D=2.1\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 9: Typ. transfer characteristics



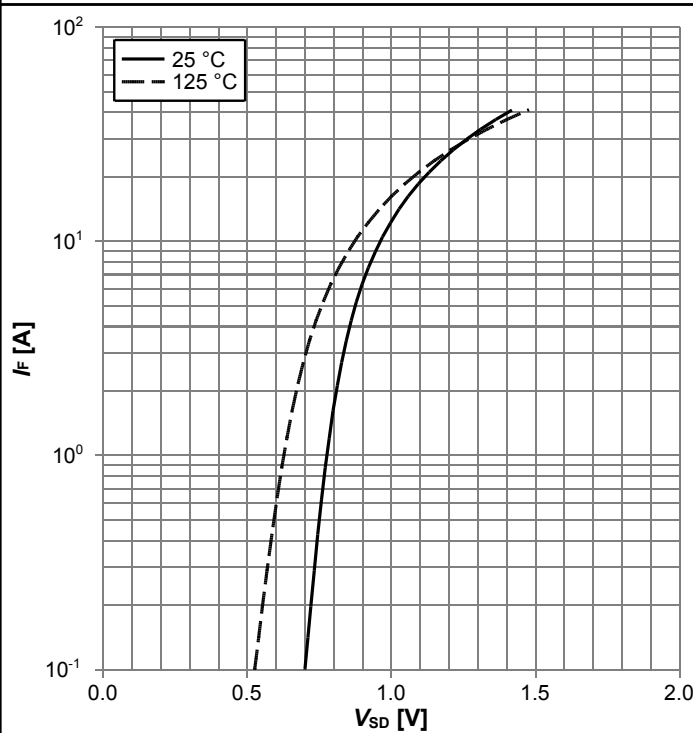
$I_D=f(V_{GS}); V_{DS}=20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



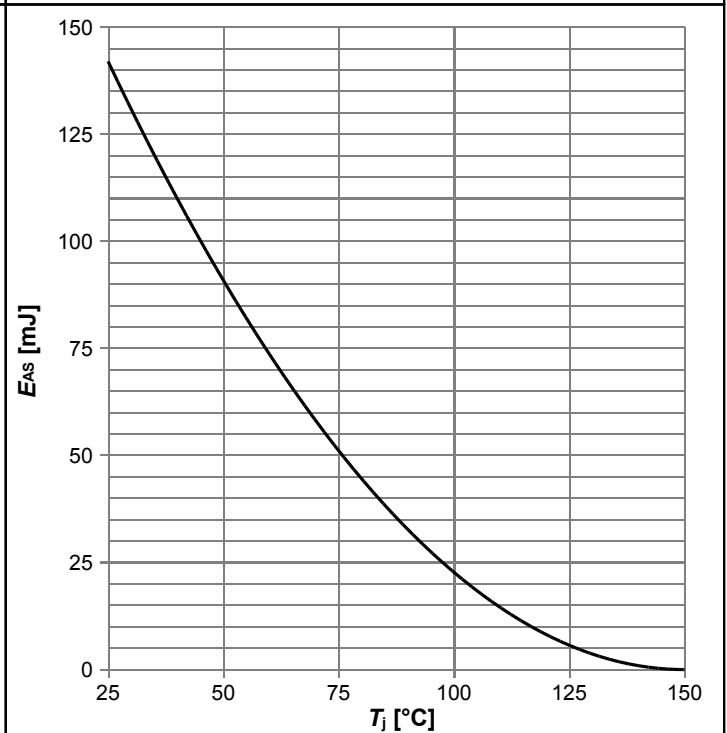
$V_{GS}=f(Q_{gate}); I_D=3.2 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



$I_F=f(V_{SD}); \text{parameter: } T_j$

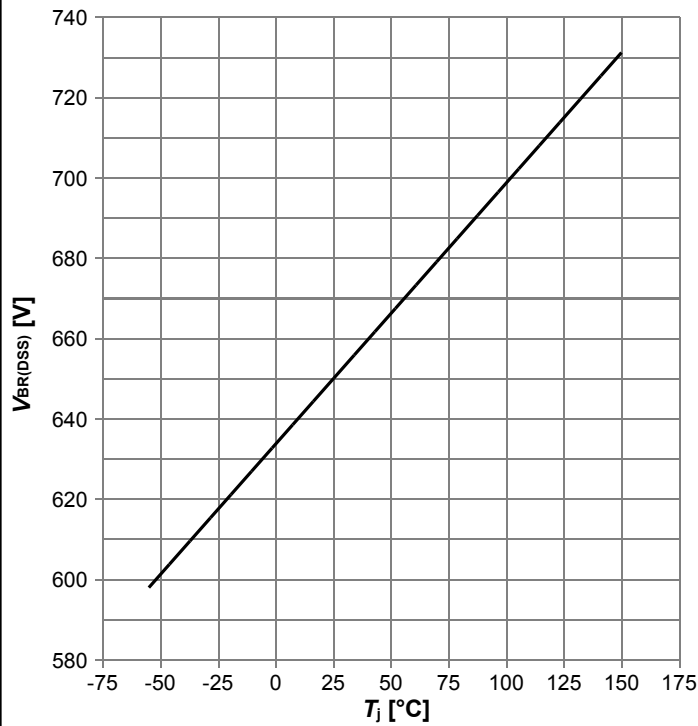
Diagram 12: Avalanche energy



$E_{AS}=f(T_j); I_D=1.3 \text{ A}; V_{DD}=50 \text{ V}$

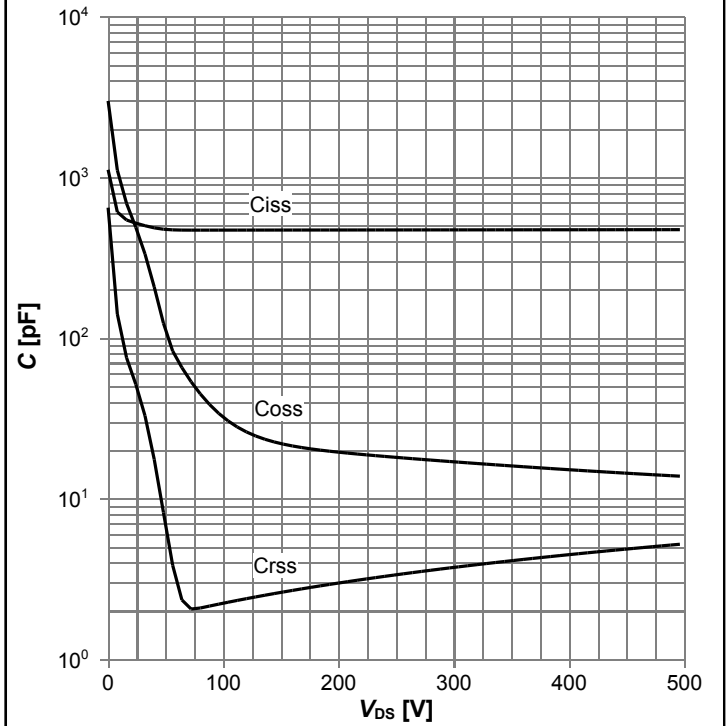
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Diagram 13: Drain-source breakdown voltage



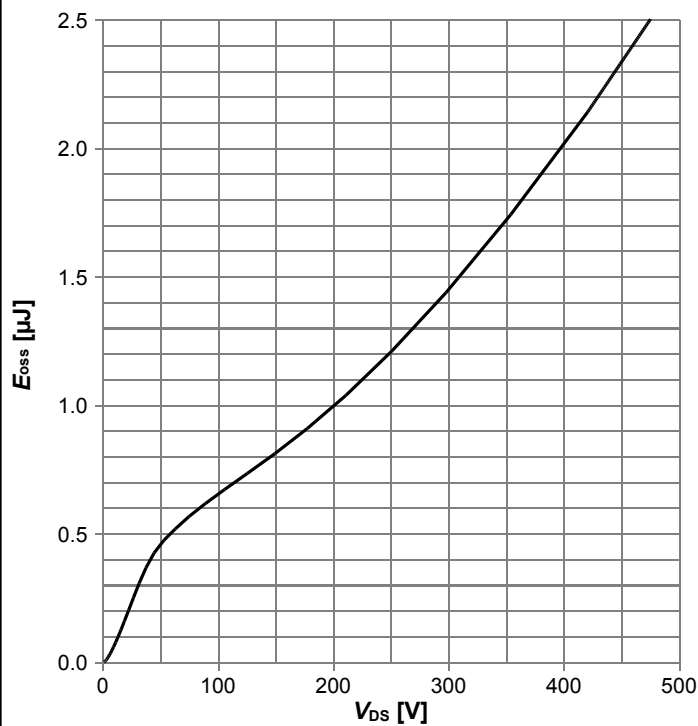
$V_{BR(DSS)}=f(T_j); I_D=1.0 \text{ mA}$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=1 \text{ MHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

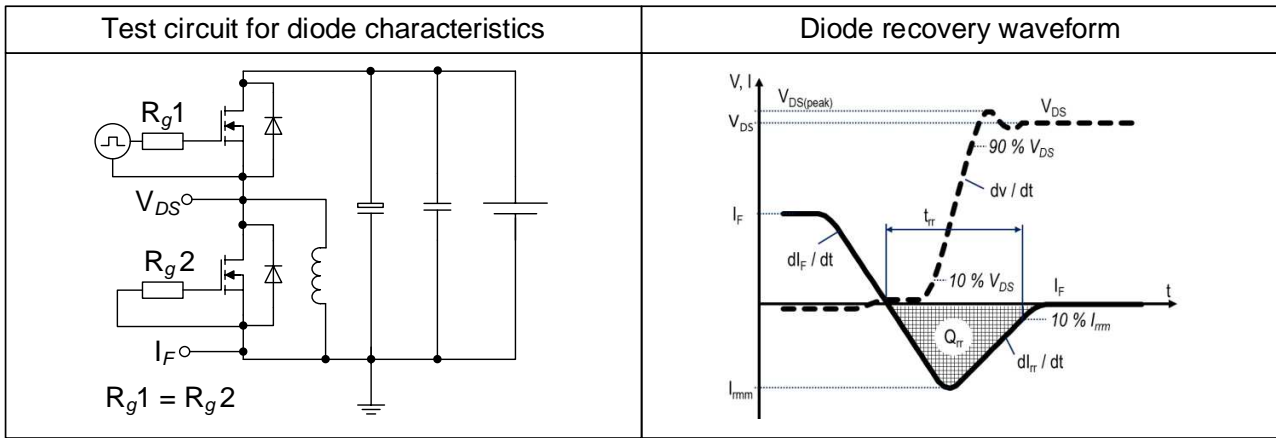


Table 9 Switching times

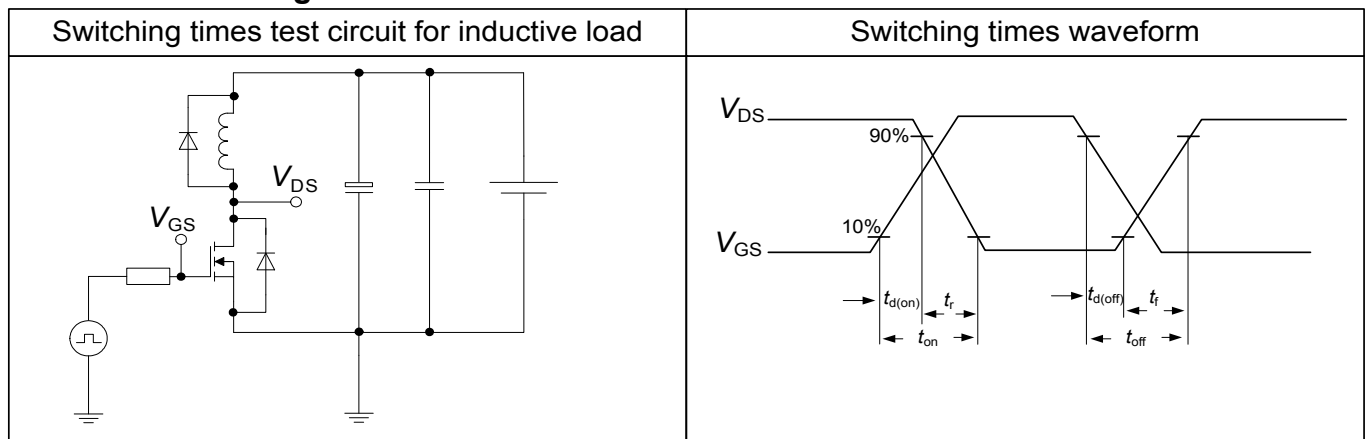
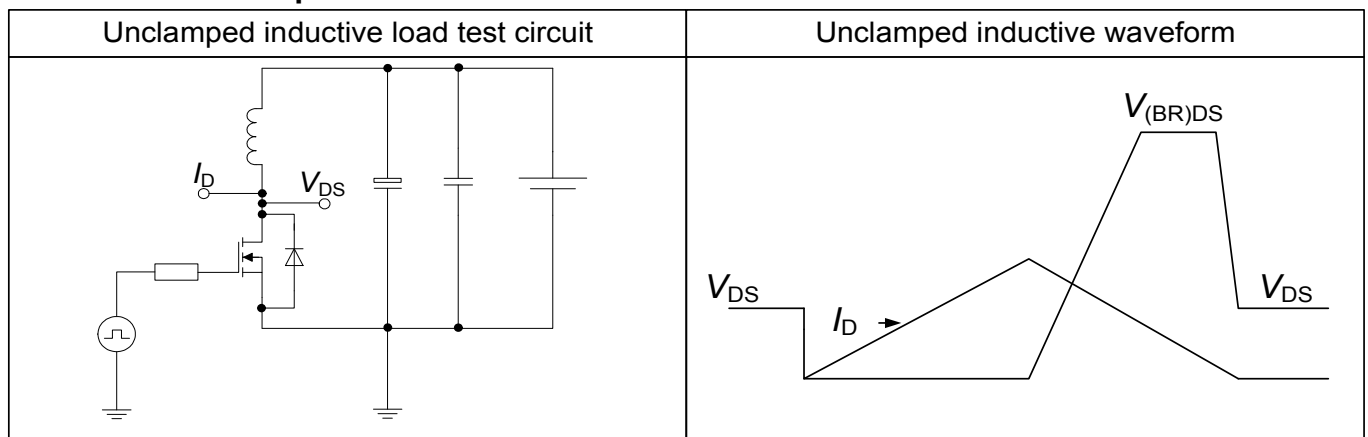
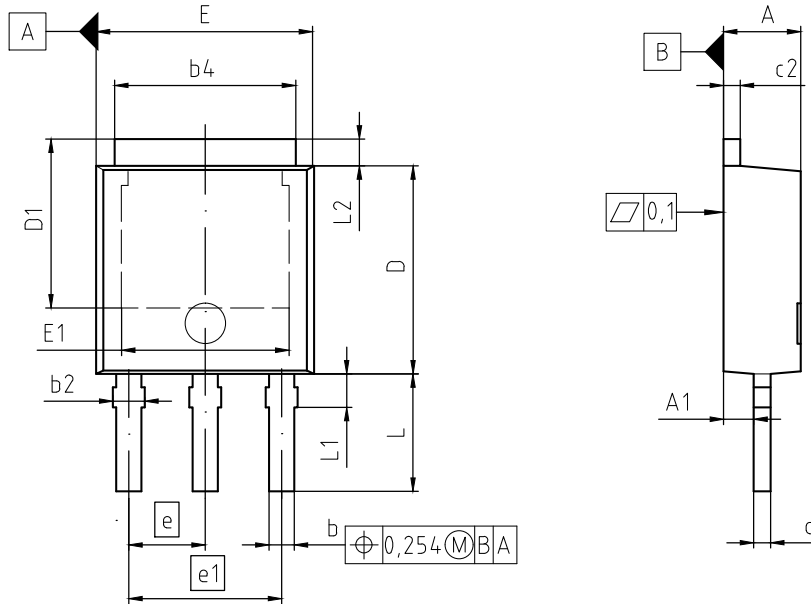


Table 10 Unclamped inductive load



6 Package Outlines



NOTES:

1. INDUSTRIAL QUALITY GRADE
2. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-251 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.35	0.087	0.093
A1	0.80	1.14	0.031	0.044
b	0.64	0.89	0.026	0.033
b2	0.65	1.15	0.026	0.045
b4	5.20	5.50	0.205	0.217
c	0.46	0.59	0.018	0.023
c2	0.46	0.89	0.018	0.023
D	6.00	6.22	0.236	0.245
D1	5.04	5.55	0.198	0.219
E	6.45	6.70	0.254	0.264
E1	4.60	5.10	0.181	0.201
e	2.28		0.090	
e1	4.56		0.180	
N	3		3	
L	3.00	3.60	0.118	0.142
L1	0.80	1.20	0.031	0.047
L2	0.90	1.25	0.035	0.049

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Figure 1 Outline PG-TO 251-3, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ E6 Webpage: www.infineon.com
- IFX CoolMOS™ E6 application note: www.infineon.com
- IFX CoolMOS™ E6 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPS65R600E6

Revision: 2017-07-27, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2015-04-23	Release of final version
2.1	2017-07-27	Updated package drawing on page 12

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